

Hiroki Hibino

List of Publications by Year in descending order

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papers

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times ranked

7794
citing authors

#	ARTICLE	IF	CITATIONS
1	Theoretical study on role of edge termination for growth direction selectivity in chemical vapor deposition of hBN/graphene heterostructure on Cu surface. Applied Physics Express, 2021, 14, 085502.	2.4	3
2	Epitaxial Intercalation Growth of Scalable Hexagonal Boron Nitride/Graphene Bilayer Moiré Materials with Highly Convergent Interlayer Angles. ACS Nano, 2021, 15, 14384-14393.	14.6	14
3	Controlled CVD growth of lateral and vertical graphene/h-BN heterostructures. Applied Physics Express, 2020, 13, 065007.	2.4	10
4	In-situ X-ray diffraction analysis of GaN growth on graphene-covered amorphous substrates. Japanese Journal of Applied Physics, 2020, 59, 070902.	1.5	4
5	Isothermal Growth and Stacking Evolution in Highly Uniform Bernal-Stacked Bilayer Graphene. ACS Nano, 2020, 14, 6834-6844.	14.6	28
6	Surface-enhanced Raman scattering from buffer layer under graphene on SiC in a wide energy range from visible to near-infrared. Japanese Journal of Applied Physics, 2020, 59, 040902.	1.5	6
7	Quantum limit cyclotron resonance in monolayer epitaxial graphene in magnetic fields up to 560 T: The relativistic electron and hole asymmetry. Physical Review B, 2020, 101, .	3.2	7
8	Theoretical Study on C Adsorbate at Graphene/Cu(111) or h-BN/Cu(111) Interfaces. E-Journal of Surface Science and Nanotechnology, 2020, 18, 70-75.	0.4	5
9	Atomically Controlled Surfaces, Interfaces and Nanostructures/Scanning Probe Microscopy. Japanese Journal of Applied Physics, 2019, 58, S10001.	1.5	0
10	Synthesis of sub-millimeter single-crystal grains of aligned hexagonal boron nitride on an epitaxial Ni film. Nanoscale, 2019, 11, 14668-14675.	5.6	16
11	STM/S observations of graphene on SiC(0001) etched by H-plasma. Japanese Journal of Applied Physics, 2019, 58, S11A13.	1.5	1
12	Visualization of three different phases in a multiphase steel by scanning electron microscopy at 1 eV landing energy. Ultramicroscopy, 2019, 204, 1-5.	1.9	6
13	Catalyst-Selective Growth of Single-Orientation Hexagonal Boron Nitride toward High-Performance Atomically Thin Electric Barriers. Advanced Materials, 2019, 31, e1900880.	21.0	21
14	Dopamine detection on activated reaction field consisting of graphene-integrated silicon photonic cavity. Optics Express, 2019, 27, 32058.	3.4	5
15	In-situ Observations of Growth of 2D Layered Materials using Low-Energy Electron Microscopy. Vacuum and Surface Science, 2019, 62, 623-628.	0.1	0
16	Ultrafast Terahertz Nonlinear Optics of Landau Level Transitions in a Monolayer Graphene. Physical Review Letters, 2018, 120, 107401.	7.8	6
17	Graphene nanoribbon field-effect transistors fabricated by etchant-free transfer from Au(788). Applied Physics Letters, 2018, 112, .	3.3	29
18	Unraveling localized states in quasi free standing monolayer graphene by means of Density Functional Theory. Carbon, 2018, 130, 466-474.	10.3	7

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19	Grain Boundaries and Gas Barrier Property of Graphene Revealed by Dark-Field Optical Microscopy. Journal of Physical Chemistry C, 2018, 122, 902-910.	3.1	9
20	Atomic and electronic structure of Si dangling bonds in quasi-free-standing monolayer graphene. Nano Research, 2018, 11, 864-873.	10.4	14
21	Surface-Mediated Aligned Growth of Monolayer MoS ₂ and In-Plane Heterostructures with Graphene on Sapphire. ACS Nano, 2018, 12, 10032-10044.	14.6	64
22	Surface structures of graphene covered Cu(103). Japanese Journal of Applied Physics, 2018, 57, 100301.	1.5	1
23	Orientation-controlled growth of hexagonal boron nitride monolayers templated from graphene edges. Applied Physics Express, 2017, 10, 055102.	2.4	17
24	Behavior and role of superficial oxygen in Cu for the growth of large single-crystalline graphene. Applied Surface Science, 2017, 408, 142-149.	6.1	32
25	Very Gradual and Anomalous Oxidation at the Interface of Hydrogen-Intercalated Graphene/4H-SiC(0001). Journal of Physical Chemistry C, 2017, 121, 26389-26396.	3.1	1
26	Effects of environmental conditions on the ultrafast carrier dynamics in graphene revealed by terahertz spectroscopy. Physical Review B, 2017, 95, .	3.2	17
27	Energy Dissipation in Graphene Mechanical Resonators with and without Free Edges. Micromachines, 2016, 7, 158.	2.9	14
28	Theoretical Study of Graphene on SiC(11-20) a-Face. E-Journal of Surface Science and Nanotechnology, 2016, 14, 113-120.	0.4	1
29	Graphene optical modulator on silicon waveguide controlled by fine metal-top gate. , 2016, , .		0
30	Direct growth of graphene on SiC(0001) by KrF-excimer-laser irradiation. Applied Physics Letters, 2016, 108, 093107.	3.3	8
31	Effects of environmental changes on the carrier dynamics in graphene revealed by terahertz spectroscopy. , 2016, , .		0
32	Quantum Hall effect in epitaxial graphene with permanent magnets. Scientific Reports, 2016, 6, 38393.	3.3	9
33	Ultra-fine metal gate operated graphene optical intensity modulator. Applied Physics Letters, 2016, 109, .	3.3	9
34	Applying strain into graphene by SU-8 resist shrinkage. Journal Physics D: Applied Physics, 2016, 49, 285303.	2.8	3
35	Etchant-free graphene transfer using facile intercalation of alkanethiol self-assembled molecules at graphene/metal interfaces. Nanoscale, 2016, 8, 11503-11510.	5.6	11
36	Graphene FRET Aptasensor. ACS Sensors, 2016, 1, 710-716.	7.8	30

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37	Spatially Controlled Nucleation of Single-Crystal Graphene on Cu Assisted by Stacked Ni. ACS Nano, 2016, 10, 11196-11204.	14.6	43
38	Atmospheric Pressure Chemical Vapor Deposition Growth of Millimeter-Scale Single-Crystalline Graphene on the Copper Surface with a Native Oxide Layer. Chemistry of Materials, 2016, 28, 4893-4900.	6.7	52
39	Growth and low-energy electron microscopy characterizations of graphene and hexagonal boron nitride. Progress in Crystal Growth and Characterization of Materials, 2016, 62, 155-176.	4.0	20
40	Highly Uniform Bilayer Graphene on Epitaxial Cu-Ni(111) Alloy. Chemistry of Materials, 2016, 28, 4583-4592.	6.7	103
41	Ultrafast terahertz nonlinear effect of Landau level transition in graphene. , 2016, , .		0
42	Integrated graphene sensor on high-Q silicon-ring resonator for neurotransmitter detection. , 2016, , .		0
43	Probing the extended-state width of disorder-broadened Landau levels in epitaxial graphene. Physical Review B, 2015, 92, .	3.2	14
44	On-chip FRET Graphene Oxide Aptasensor: Quantitative Evaluation of Enhanced Sensitivity by Aptamer with a Double-stranded DNA Spacer. Analytical Sciences, 2015, 31, 875-879.	1.6	17
45	Effects of Photoexcitation on Intense Terahertz Field-induced Nonlinearity in Monolayer Epitaxial Graphene. , 2015, , .		0
46	Photocurrent generation of a single-gate graphene p-n junction fabricated by interfacial modification. Nanotechnology, 2015, 26, 385203.	2.6	15
47	Epitaxial CVD growth of high-quality graphene and recent development of 2D heterostructures. , 2015, , .		0
48	Direct growth of patterned graphene on SiC(0001) surfaces by KrF excimer-laser irradiation. , 2015, , .		0
49	Applying a large strain into graphene using thermal shrinkage of SU-8 resist. , 2015, , .		0
50	Synthesis and functionalization of two-dimensional materials: Graphene, hexagonal boron nitride, and transition metal dichalcogenides. , 2015, , .		1
51	Effects of UV light intensity on electrochemical wet etching of SiC for the fabrication of suspended graphene. Japanese Journal of Applied Physics, 2015, 54, 036502.	1.5	3
52	Nonlinear terahertz field-induced carrier dynamics in photoexcited epitaxial monolayer graphene. Physical Review B, 2015, 91, .	3.2	60
53	Large optical anisotropy for terahertz light of stacked graphene ribbons with slight asymmetry. Journal of Applied Physics, 2015, 117, 174302.	2.5	2
54	Growth Dynamics of Single-Layer Graphene on Epitaxial Cu Surfaces. Chemistry of Materials, 2015, 27, 5377-5385.	6.7	65

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55	Bilayer-induced asymmetric quantum Hall effect in epitaxial graphene. <i>Semiconductor Science and Technology</i> , 2015, 30, 055007.	2.0	7
56	Growth and Optical Properties of High-Quality Monolayer WS ₂ on Graphite. <i>ACS Nano</i> , 2015, 9, 4056-4063.	14.6	162
57	Shot noise generated by graphene p-n junctions in the quantum Hall effect regime. <i>Nature Communications</i> , 2015, 6, 8068.	12.8	34
58	On-chip graphene oxide aptasensor for multiple protein detection. <i>Analytica Chimica Acta</i> , 2015, 866, 1-9.	5.4	42
59	<i>In situ</i> scanning electron microscopy of graphene nucleation during segregation of carbon on polycrystalline Ni substrate. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 455301.	2.8	11
60	Plasmon transport and its guiding in graphene. <i>New Journal of Physics</i> , 2014, 16, 063055.	2.9	10
61	Nonlinear transmission of an intense terahertz field through monolayer graphene. <i>AIP Advances</i> , 2014, 4, 117118.	1.3	24
62	Nonlinear terahertz-field-induced carrier dynamics in photoexcited graphene. , 2014, , .		0
63	Correlation between morphology and transport properties of quasi-free-standing monolayer graphene. <i>Applied Physics Letters</i> , 2014, 105, 221604.	3.3	19
64	Etchant-free and damageless transfer of monolayer and bilayer graphene grown on SiC. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 115101.	1.5	10
65	Scalable synthesis of layer-controlled WS ₂ and MoS ₂ sheets by sulfurization of thin metal films. <i>Applied Physics Letters</i> , 2014, 105, .	3.3	107
66	Energy dissipation in edged and edgeless graphene mechanical resonators. <i>Journal of Applied Physics</i> , 2014, 116, 064304.	2.5	13
67	Influence of graphene on quality factor variation in a silicon ring resonator. <i>Applied Physics Letters</i> , 2014, 104, 091122.	3.3	19
68	Effects of hydrogen intercalation on transport properties of quasi-free-standing monolayer graphene. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 04EN01.	1.5	20
69	Stability and Reactivity of [11-20] Step in Initial Stage of Epitaxial Graphene Growth on SiC(0001). <i>Materials Science Forum</i> , 2014, 778-780, 1150-1153.	0.3	0
70	Resonant Edge Magnetoplasmons and Their Decay in Graphene. <i>Physical Review Letters</i> , 2014, 113, 266601.	7.8	48
71	Direct Chemical Vapor Deposition Growth of WS ₂ Atomic Layers on Hexagonal Boron Nitride. <i>ACS Nano</i> , 2014, 8, 8273-8277.	14.6	267
72	Ultrathin Chemical Vapor Deposition (CVD)-Grown Hexagonal Boron Nitride as a High-Quality Dielectric for Tunneling Devices on Rigid and Flexible Substrates. <i>Journal of Physical Chemistry C</i> , 2014, 118, 3340-3346.	3.1	26

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73	Raman spectroscopic investigation of polycrystalline structures of CVD-grown graphene by isotope labeling. <i>Nanoscale</i> , 2014, 6, 13838-13844.	5.6	21
74	Formation of Oriented Graphene Nanoribbons over Heteroepitaxial Cu Surfaces by Chemical Vapor Deposition. <i>Chemistry of Materials</i> , 2014, 26, 5215-5222.	6.7	9
75	Optical absorption characteristics and polarization dependence of single-layer graphene on silicon waveguide. <i>IEICE Transactions on Electronics</i> , 2014, E97.C, 736-743.	0.6	0
76	Theoretical studies of graphene on SiC. , 2014, , .		0
77	Surface-Enhanced Raman Scattering of Graphene on SiC by Gold Nanoparticles. <i>The Review of Laser Engineering</i> , 2014, 42, 652.	0.0	1
78	Temperature Dependence of Terahertz Transmission through Photoexcited Graphene. , 2014, , .		0
79	Boron nitride growth on metal foil using solid sources. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013, 31, .	1.2	15
80	Hydrogen storage with titanium-functionalized graphene. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	55
81	Site-Selective Epitaxy of Graphene on Si Wafers. <i>Proceedings of the IEEE</i> , 2013, 101, 1557-1566.	21.3	13
82	Molecular design for enhanced sensitivity of a FRET aptasensor built on the graphene oxide surface. <i>Chemical Communications</i> , 2013, 49, 10346-10348.	4.1	32
83	Core-level photoelectron spectroscopy study of interface structure of hydrogen-intercalated graphene onn-type 4H-SiC(0001). <i>Physical Review B</i> , 2013, 88, .	3.2	12
84	Structural Instability of Transferred Graphene Grown by Chemical Vapor Deposition against Heating. <i>Journal of Physical Chemistry C</i> , 2013, 117, 22123-22130.	3.1	22
85	Lattice-Oriented Catalytic Growth of Graphene Nanoribbons on Heteroepitaxial Nickel Films. <i>ACS Nano</i> , 2013, 7, 10825-10833.	14.6	27
86	Graphene-Based Nano-Electro-Mechanical Switch with High On/Off Ratio. <i>Applied Physics Express</i> , 2013, 6, 055101.	2.4	28
87	Plasmon transport in graphene investigated by time-resolved electrical measurements. <i>Nature Communications</i> , 2013, 4, 1363.	12.8	46
88	Molecular beam epitaxial growth of graphene using cracked ethylene. <i>Journal of Crystal Growth</i> , 2013, 378, 404-409.	1.5	2
89	Molecular beam epitaxial growth of graphene using cracked ethylene “ Advantage over ethanol in growth. <i>Diamond and Related Materials</i> , 2013, 34, 84-88.	3.9	11
90	Protein recognition on a single graphene oxide surface fixed on a solid support. <i>Journal of Materials Chemistry B</i> , 2013, 1, 1119.	5.8	29

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91	Growth and low-energy electron microscopy characterization of monolayer hexagonal boron nitride on epitaxial cobalt. Nano Research, 2013, 6, 335-347.	10.4	108
92	Quantum Faraday and Kerr rotations in graphene. Nature Communications, 2013, 4, 1841.	12.8	167
93	Infrared cyclotron resonances of Dirac electrons in SiC epitaxial graphene in ultra-high magnetic fields. , 2013, , .		0
94	Role of step in initial stage of graphene growth on SiC(0001). , 2013, , .		0
95	Graphene Layer Formation on Polycrystalline Nickel Grown by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2013, 52, 035103.	1.5	12
96	Epitaxial Trilayer Graphene Mechanical Resonators Obtained by Electrochemical Etching Combined with Hydrogen Intercalation. Japanese Journal of Applied Physics, 2013, 52, 04CH01.	1.5	13
97	Characterization of Optical Absorption and Polarization Dependence of Single-Layer Graphene Integrated on a Silicon Wire Waveguide. Japanese Journal of Applied Physics, 2013, 52, 060203.	1.5	29
98	Intense terahertz-field-induced nonlinearity in graphene. , 2013, , .		0
99	Self organization of a hexagonal network of quasi-free-standing monolayer graphene nanoribbons. Physical Review B, 2013, 87, .	3.2	5
100	Stability and reactivity of steps in the initial stage of graphene growth on the SiC(0001) surface. Physical Review B, 2013, 88, .	3.2	16
101	Selective charge doping of chemical vapor deposition-grown graphene by interface modification. Applied Physics Letters, 2013, 103, .	3.3	16
102	Tuning of quantum interference in top-gated graphene on SiC. Physical Review B, 2013, 88, .	3.2	15
103	Graphene-modified Interdigitated Array Electrode: Fabrication, Characterization, and Electrochemical Immunoassay Application. Analytical Sciences, 2013, 29, 55-60.	1.6	28
104	Formation of Graphene Nanofin Networks on Graphene/SiC(0001) by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 06FD16.	1.5	0
105	Electrical Characterization of Bilayer Graphene Formed by Hydrogen Intercalation of Monolayer Graphene on SiC(0001). Japanese Journal of Applied Physics, 2012, 51, 02BN02.	1.5	17
106	Impact of graphene quantum capacitance on transport spectroscopy. Physical Review B, 2012, 86, .	3.2	26
107	Quantum Hall Effect and Carrier Scattering in Quasi-Free-Standing Monolayer Graphene. Applied Physics Express, 2012, 5, 125101.	2.4	28
108	The physics of epitaxial graphene on SiC(0001). Journal of Physics Condensed Matter, 2012, 24, 314215.	1.8	23

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109	In-situ Observation of Graphene Growth on Ultra Flat Metal Substrates. Hyomen Kagaku, 2012, 33, 557-562.	0.0	0
110	Self-spreading of Supported Lipid Bilayer on SiO ₂ Surface Bearing Graphene Oxide. Chemistry Letters, 2012, 41, 1259-1261.	1.3	20
111	Catalytic Growth of Graphene: Toward Large-Area Single-Crystalline Graphene. Journal of Physical Chemistry Letters, 2012, 3, 2228-2236.	4.6	136
112	Growth and electronic transport properties of epitaxial graphene on SiC. Journal Physics D: Applied Physics, 2012, 45, 154008.	2.8	38
113	Graphene Growth from Spin-Coated Polymers without a Gas. Japanese Journal of Applied Physics, 2012, 51, 06FD01.	1.5	0
114	In situ scanning electron microscopy of graphene growth on polycrystalline Ni substrate. Surface Science, 2012, 606, 728-732.	1.9	61
115	Microscopic Raman Mapping of Epitaxial Graphene on 4H-SiC(0001). Japanese Journal of Applied Physics, 2012, 51, 06FD06.	1.5	3
116	A Raman imaging study of growth process of few-layer epitaxial graphene on vicinal 6H-SiC. Diamond and Related Materials, 2012, 25, 80-83.	3.9	2
117	Domain Structure and Boundary in Single-Layer Graphene Grown on Cu(111) and Cu(100) Films. Journal of Physical Chemistry Letters, 2012, 3, 219-226.	4.6	209
118	Macroscopic Single-Domain Graphene Growth on Polycrystalline Nickel Surface. Applied Physics Express, 2012, 5, 035501.	2.4	18
119	Spatially Resolved Compositional Analysis of a BCN Thin Film Grown on a Ni Substrate by Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 2012, 1451, 151-156.	0.1	0
120	Growth of atomically thin hexagonal boron nitride films by diffusion through a metal film and precipitation. Journal Physics D: Applied Physics, 2012, 45, 385304.	2.8	44
121	Chemical Vapor Deposition of Hexagonal Boron Nitride. E-Journal of Surface Science and Nanotechnology, 2012, 10, 133-138.	0.4	17
122	Influence of Cu metal on the domain structure and carrier mobility in single-layer graphene. Carbon, 2012, 50, 2189-2196.	10.3	86
123	Chemical vapor deposition of boron- and nitrogen-containing graphene thin films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 233-238.	3.5	25
124	Electrical Characterization of Bilayer Graphene Formed by Hydrogen Intercalation of Monolayer Graphene on SiC(0001). Japanese Journal of Applied Physics, 2012, 51, 02BN02.	1.5	29
125	Microscopic Raman Mapping of Epitaxial Graphene on 4H-SiC(0001). Japanese Journal of Applied Physics, 2012, 51, 06FD06.	1.5	5
126	Formation of Graphene Nanofin Networks on Graphene/SiC(0001) by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 06FD16.	1.5	1

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127	Near-Infrared Photoluminescence Spectral Imaging of Chemically Oxidized Graphene Flakes. E-Journal of Surface Science and Nanotechnology, 2012, 10, 513-517.	0.4	1
128	Nanocarbon Materials Growth Dependent on Au Nanoparticle Catalyst Size. Hyomen Kagaku, 2012, 33, 141-146.	0.0	0
129	Graphene Growth from Spin-Coated Polymers without a Gas. Japanese Journal of Applied Physics, 2012, 51, 06FD01.	1.5	1
130	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. Japanese Journal of Applied Physics, 2011, 50, 070115.	1.5	8
131	Atomic Structure of Epitaxial Graphene Islands on SiC(0001) Surfaces and their Magnetoelectric Effects. , 2011, , .		0
132	Characterization of doped single-wall carbon nanotubes by Raman spectroscopy. Carbon, 2011, 49, 2264-2272.	10.3	55
133	Study of Graphene Growth by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol: Influence of Gas Flow Rate on Graphitic Material Deposition. Japanese Journal of Applied Physics, 2011, 50, 06GE12.	1.5	8
134	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. Japanese Journal of Applied Physics, 2011, 50, 095601.	1.5	8
135	Observation of Band Gap in Epitaxial Bilayer Graphene Field Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DN04.	1.5	16
136	Pattern formation of a step induced by a moving linear source. Physical Review B, 2011, 84, .	3.2	6
137	Carrier transport mechanism in graphene on SiC(0001). Physical Review B, 2011, 84, .	3.2	85
138	Graphene Growth from a Spin-Coated Polymer without a Reactive Gas. Applied Physics Express, 2011, 4, 065102.	2.4	18
139	Electronic transport properties of top-gated monolayer and bilayer graphene devices on SiC. Materials Research Society Symposia Proceedings, 2011, 1283, 1.	0.1	2
140	Molecular beam epitaxial growth of graphene and ridge-structure networks of graphene. Journal Physics D: Applied Physics, 2011, 44, 435305.	2.8	13
141	Evaluation of Few-Layer Graphene Grown by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol. E-Journal of Surface Science and Nanotechnology, 2011, 9, 58-62.	0.4	9
142	Observation of Band Gap in Epitaxial Bilayer Graphene Field Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DN04.	1.5	3
143	Study of Graphene Growth by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol: Influence of Gas Flow Rate on Graphitic Material Deposition. Japanese Journal of Applied Physics, 2011, 50, 06GE12.	1.5	23
144	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. Japanese Journal of Applied Physics, 2011, 50, 070115.	1.5	9

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145	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. Japanese Journal of Applied Physics, 2011, 50, 095601.	1.5	9
146	Contact Conductance Measurement of Locally Suspended Graphene on SiC. Applied Physics Express, 2010, 3, 045101.	2.4	20
147	Growth of few-layer graphene by gas-source molecular beam epitaxy using cracked ethanol. Physica Status Solidi (B): Basic Research, 2010, 247, 916-920.	1.5	4
148	Atomic Structure and Physical Properties of Epitaxial Graphene Islands Embedded in SiC(0001) Surfaces. Applied Physics Express, 2010, 3, 115103.	2.4	10
149	Dynamics of Si Surface Morphology. , 2010, , .		0
150	Thin Graphitic Structure Formation on Various Substrates by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol. Japanese Journal of Applied Physics, 2010, 49, 04DH13.	1.5	30
151	Epitaxial few-layer graphene: towards single crystal growth. Journal Physics D: Applied Physics, 2010, 43, 374005.	2.8	106
152	Anisotropic layer-by-layer growth of graphene on vicinal SiC(0001) surfaces. Physical Review B, 2010, 81, .	3.2	99
153	Half-Integer Quantum Hall Effect in Gate-Controlled Epitaxial Graphene Devices. Applied Physics Express, 2010, 3, 075102.	2.4	64
154	Analysis of Number of Layers in Epitaxial Few-Layer Graphene Grown on SiC towards Single-Crystal Graphene Substrate. Journal of the Vacuum Society of Japan, 2010, 53, 101-108.	0.3	0
155	Local conductance measurements of double-layer graphene on SiC substrate. Nanotechnology, 2009, 20, 445704.	2.6	38
156	Dependence of electronic properties of epitaxial few-layer graphene on the number of layers investigated by photoelectron emission microscopy. Physical Review B, 2009, 79, .	3.2	246
157	Stacking domains of epitaxial few-layer graphene on SiC(0001). Physical Review B, 2009, 80, .	3.2	84
158	A Lattice Model for Thermal Decoration and Step Bunching in Vicinal Surface with Sub-Monolayer Adsorbates. E-Journal of Surface Science and Nanotechnology, 2009, 7, 39-44.	0.4	9
159	Two-dimensional emission patterns of secondary electrons from graphene layers formed on SiC(0001). Applied Surface Science, 2008, 254, 7596-7599.	6.1	20
160	Instability of steps during Ga deposition on Si(111). Surface Science, 2008, 602, 2421-2426.	1.9	14
161	Oxide-mediated formation of $\sqrt{3}\times\sqrt{3}$ -FeSi ₂ on Si(001) studied by X-ray adsorption near edge structure analysis using SPELEEM. Surface and Interface Analysis, 2008, 40, 1747-1750.	1.8	3
162	Mechanism of Gold-Catalyzed Carbon Material Growth. Nano Letters, 2008, 8, 832-835.	9.1	112

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163	In-plane conductance measurement of graphene nanoislands using an integrated nanogap probe. Nanotechnology, 2008, 19, 495701.	2.6	22
164	Microscopic thickness determination of thin graphite films formed on SiC from quantized oscillation in reflectivity of low-energy electrons. Physical Review B, 2008, 77, .	3.2	330
165	Local conductance measurement of few-layer graphene on SiC substrate using an integrated nanogap probe. Journal of Physics: Conference Series, 2008, 100, 052006.	0.4	8
166	Thickness Determination of Graphene Layers Formed on SiC Using Low-Energy Electron Microscopy. E-Journal of Surface Science and Nanotechnology, 2008, 6, 107-110.	0.4	46
167	Self-assembly of vesicle nanoarrays on Si: A potential route to high-density functional protein arrays. Applied Physics Letters, 2007, 90, 033901.	3.3	5
168	Boron Nitride Thin Films Grown on Graphitized 6H-SiC Substrates by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2007, 46, 2554-2557.	1.5	15
169	Carbon Nanotube Growth from Semiconductor Nanoparticles. Nano Letters, 2007, 7, 2272-2275.	9.1	224
170	Single-Walled Carbon Nanotube Growth from Highly Activated Metal Nanoparticles. Nano Letters, 2006, 6, 2642-2645.	9.1	413
171	Surface Reactions of Metal Catalysts for Carbon Nanotubes on an Oxide Thin Layer/Si Substrates Studied by in-situ Micro X-ray Adsorption Spectroscopy using SPELEEM. Materials Research Society Symposia Proceedings, 2006, 967, 1.	0.1	0
172	Void growth during thermal decomposition of silicon oxide layers studied by low-energy electron microscopy. Journal of Applied Physics, 2006, 100, 113519.	2.5	38
173	Vertical GaP nanowires arranged at atomic steps on Si(111) substrates. Applied Physics Letters, 2006, 89, 033114.	3.3	33
174	Surface Reactions of Co on SiO ₂ thin layer/Si substrate Studied by LEEM and PEEM. E-Journal of Surface Science and Nanotechnology, 2006, 4, 155-160.	0.4	6
175	Arrangement of Au-Si alloy islands at atomic steps. Surface Science, 2005, 588, L233-L238.	1.9	27
176	Ultrahigh vacuum scanning electron microscope system combined with wide-movable scanning tunneling microscope. Review of Scientific Instruments, 2005, 76, 083709.	1.3	6
177	Growth of Twinned Epitaxial Layers on Si(111) $\sqrt{3}\times\sqrt{3}$ -B Studied by Low-Energy Electron Microscopy. Japanese Journal of Applied Physics, 2005, 44, 358-364.	1.5	9
178	Thermal decay of superheated 7\AA - 7\AA islands and supercooled 1\AA - 1\AA vacancy islands on Si(111). Physical Review B, 2005, 72, .	3.2	8
179	Site-controlled InP nanowires grown on patterned Si substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 24, 133-137.	2.7	33
180	Structural and morphological changes on surfaces with multiple phases studied by low-energy electron microscopy. Applied Surface Science, 2004, 237, 51-57.	6.1	5

#	ARTICLE	IF	CITATIONS
181	Step wandering due to the gap in diffusion coefficient on the upper and the lower terraces. Surface Science, 2003, 522, 64-74.	1.9	17
182	Step wandering induced by homoepitaxy on Si(111) during $(1 \times 1) \rightarrow (7 \times 7)$ phase transition. Surface Science, 2003, 527, L222-L228.	1.9	22
183	Ultrafine and Well-Defined Patterns on Silicon Through Reaction Selectivity. Advanced Materials, 2002, 14, 1418-1421.	21.0	6
184	Design of Si surfaces for self-assembled nanoarchitecture. Surface Science, 2002, 514, 1-9.	1.9	21
185	Hysteresis in the $(1 \times 1) \rightarrow (7 \times 7)$ first-order phase transition on the Si(111) surface. Surface Science, 2001, 487, 191-200.	1.9	24
186	Growth of Si twinning superlattice. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 87, 214-221.	3.5	12
187	Diffusion barrier caused by (1×1) and (7×7) on Si(111) during phase transition. Physical Review B, 2001, 64, .	3.2	16
188	Controlled striped phase formation on ultraflat Si(001) surfaces during diborane exposure. Applied Physics Letters, 2001, 79, 3857-3859.	3.3	7
189	Decay kinetics of two-dimensional islands and holes on Si(111) studied by low-energy electron microscopy. Physical Review B, 2001, 63, .	3.2	60
190	Enhanced Terrace Stability for Preparation of Step-Free Si(001) (2×1) Surfaces. Physical Review Letters, 2001, 87, 136103.	7.8	13
191	RHEED analysis of twinned homoepitaxial layers grown on Si(111) $(\sqrt{3} \times \sqrt{3})$. Thin Solid Films, 2000, 369, 5-9.	1.8	5
192	Dynamics of the silicon (111) surface phase transition. Nature, 2000, 405, 552-554.	27.8	53
193	Observation of Incomplete Surface Melting of Si Using Medium-Energy Ion Scattering Spectroscopy. Japanese Journal of Applied Physics, 2000, 39, 4421-4424.	1.5	6
194	Transformation of surface structures on vicinal Si(111) during heating. Surface Science, 2000, 445, 327-334.	1.9	5
195	Si Twinning Superlattice Growth of New Single Crystal Si. Surface Review and Letters, 2000, 7, 631-635.	1.1	1
196	Origin of Reducing Domain Boundaries of Si(111)- (7×7) during Homoepitaxial Growth. Japanese Journal of Applied Physics, 1999, 38, 1530-1533.	1.5	2
197	Kinetics and Thermodynamics of Surface Steps on Semiconductors. Critical Reviews in Solid State and Materials Sciences, 1999, 24, 227-263.	12.3	18
198	Fabrication and Integration of Nanostructures on Si Surfaces. Accounts of Chemical Research, 1999, 32, 447-454.	15.6	46

#	ARTICLE	IF	CITATIONS
199	Step Bunching during SiGe Growth on Vicinal Si(111) Surfaces. Materials Research Society Symposia Proceedings, 1999, 584, 77.	0.1	2
200	Transformation of Artificial Structures on Silicon Surface due to Evaporation.. Hyomen Kagaku, 1999, 20, 859-864.	0.0	0
201	Sublimation of Si(111) Surfaces Observed by Ultrahigh Vacuum Scanning Electron Microscopy.. Shinku/Journal of the Vacuum Society of Japan, 1999, 42, 79-83.	0.2	0
202	Growth process of twinned epitaxial layers on Si(111)-B and their thermal stability. Applied Surface Science, 1998, 130-132, 41-46.	6.1	7
203	Formation of twinned two-bilayer-high islands during initial stages of Si growth on Si(111)-B. Surface Science, 1998, 412-413, 132-140.	1.9	14
204	Twinned epitaxial layers formed on Si(111)-B. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 1934-1937.	2.1	33
205	Sublimation of a heavily boron-doped Si(111) surface. Physical Review B, 1998, 58, 13146-13150.	3.2	33
206	Disordering of Si(111) at high temperatures. Physical Review B, 1998, 58, 12587-12589.	3.2	17
207	Triangular-tiled arrangement of $7\sqrt{3}\text{Å}$ and 1Å domains on Si(111). Physical Review B, 1998, 58, R7500-R7503.		9
208	Self-organization at Semiconductor Surfaces. Wafer-Scale Control of Nanostructures on Si by Using Self Organization Processes.. Hyomen Kagaku, 1998, 19, 557-564.	0.0	3
209	Substitution of In for Si adatoms and exchanges between In and Si adatoms on a Si(111)- $7\sqrt{3}\text{Å}$ surface. Physical Review B, 1997, 55, 7018-7022.	3.2	11
210	Sublimation of the Si(111) surface in ultrahigh vacuum. Physical Review B, 1997, 55, R10237-R10240.	3.2	68
211	Phase transitions on Si(113): A high-temperature scanning-tunneling-microscopy study. Physical Review B, 1997, 56, 4092-4097.	3.2	22
212	Step arrangement design and nanostructure self-organization on Si surfaces. Applied Surface Science, 1997, 117-118, 642-651.	6.1	36
213	Phase transition of $12\sqrt{3}\text{Å}$ reconstruction on Si(331). Surface Science, 1996, 357-358, 102-106.	1.9	3
214	1Å to $(7\sqrt{3}\text{Å})$ phase transition on Si(111) under heating current. Surface Science, 1996, 364, L587-L590.		9
215	Erratum to "Exchanges between Si and Pb adatoms on Si(111)". [Surface Science 328 (1995) L547]. Surface Science, 1996, 364, L547.	1.9	1
216	Two-stage phase transition of $12\sqrt{3}\text{Å}$ reconstruction on Si(331). Physical Review B, 1996, 53, 15682-15687.	3.2	9

#	ARTICLE	IF	CITATIONS
217	Step arrangement design and nanostructure self-organization on Si(111) surfaces by patterning-assisted control. Applied Surface Science, 1996, 107, 1-5.	6.1	20
218	Exchanges between group-III (B, Al, Ga, In) and Si atoms on Si(111)-3 \times 3 surfaces. Physical Review B, 1996, 54, 5763-5768.	3.2	16
219	Fabrication of nanostructures on silicon surfaces on wafer scale by controlling self-organization processes. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 4134.	1.6	25
220	Reducing domain boundaries of surface reconstruction during molecular beam epitaxy on Si(111). Applied Physics Letters, 1995, 67, 915-917.	3.3	23
221	Patterning-Assisted Control for Ordered Arrangement of Atomic Steps on Si(111) Surfaces. Japanese Journal of Applied Physics, 1995, 34, L668-L670.	1.5	31
222	Real-space observation of (111) facet formation on vicinal Si(111) surfaces. Physical Review B, 1995, 51, 7753-7761.	3.2	18
223	Direct evidence for Ge preferential growth at steps and out-of-phase boundaries of (7 \times 7) domains on Si(111) in solid phase epitaxy. Surface Science, 1995, 324, L333-L336.	1.9	9
224	Exchanges between Si and Pb adatoms on Si(111). Surface Science, 1995, 328, L547-L552.	1.9	11
225	Secondary Electron Imaging of (7 \times 7) Domains on Si(111) Surfaces.. Hyomen Kagaku, 1995, 16, 415-421.	0.0	0
226	Solid Phase Epitaxy on Si Surfaces Studied by Scanning Tunneling Microscopy. Scanning-Tunneling-Microscopy Observations of Ge Solid-Phase Epitaxy on Si(111).. Hyomen Kagaku, 1995, 16, 113-120.	0.0	0
227	Transient step bunching on a vicinal Si(111) surface. Physical Review Letters, 1994, 72, 657-660.	7.8	54
228	Trace of interface reconstruction in Ge solid-phase epitaxy on Si(111). Physical Review B, 1994, 49, 5765-5768.	3.2	11
229	Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111). Applied Surface Science, 1994, 82-83, 374-379.	6.1	8
230	Pb preadsorption facilitates island formation during Ge growth on Si(111). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1994, 12, 23-28.	2.1	19
231	Real-time scanning tunneling microscopy of phase transition and faceting on a vicinal Si(111) surface. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 1640-1643.	2.1	11
232	Real-Time Observation of (1 \times 1)-(7 \times 7) Phase Transition on Vicinal Si(111) Surfaces by Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 1993, 32, 3247-3251.	1.5	20
233	High-temperature scanning-tunneling-microscopy observation of phase transitions and reconstruction on a vicinal Si(111) surface. Physical Review B, 1993, 47, 13027-13030.	3.2	74
234	Mesh pattern of Ge islands grown using solid phase epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 2458-2462.	2.1	34

#	ARTICLE	IF	CITATIONS
235	Periodic Arrangement of Ge Islands on Si(111). Materials Research Society Symposia Proceedings, 1993, 317, 41.	0.1	6
236	Initial Growth Stages of Ge on Si(111).. Hyomen Kagaku, 1993, 14, 105-112.	0.0	1
237	TEM Moiré Pattern and Scanning Auger Electron Microscope Analysis of Anomalous Si Incorporation into MBE-grown Ge on Si(111). Japanese Journal of Applied Physics, 1992, 31, 3296-3300.	1.5	4
238	Surface structural changes during the initial growth of Ge on Si(111)7 Å— 7. Applied Surface Science, 1992, 60-61, 112-119.	6.1	17
239	Step band structures on vicinal Si(111) surfaces created by DC resistive heating. Applied Surface Science, 1992, 60-61, 479-484.	6.1	18
240	Reflection High-Energy Electron Diffraction Studies of Vicinal Si(111) Surfaces. Japanese Journal of Applied Physics, 1991, 30, 1337-1342.	1.5	24
241	DC-Resistive-Heating-Induced Step Bunching on Vicinal Si (111). Japanese Journal of Applied Physics, 1990, 29, L2254-L2256.	1.5	126
242	RHEED studies on vicinal Si(111), (100) surfaces.. Hyomen Kagaku, 1990, 11, 500-506.	0.0	0
243	Theoretical Study of Epitaxial Graphene Growth on SiC(0001) Surfaces. Applied Physics Express, 0, 2, 065502.	2.4	62
244	Epitaxial Graphene Growth Studied by Low-Energy Electron Microscopy and First-Principles. Materials Science Forum, 0, 645-648, 597-602.	0.3	12
245	Correlation between structures and vibration properties of germanene grown by Ge segregation. Applied Physics Express, 0, , .	2.4	7